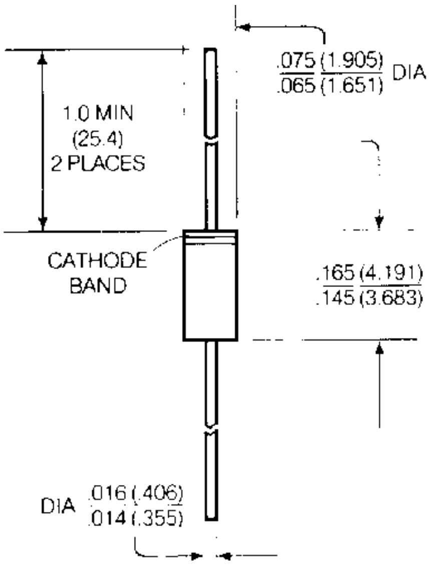
AP1000C-11

SILICON PIN DIODE

DESCRIPTION:

The **AP1000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device Iis Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

PACKAGE STYLE 01



MAXIMUM RATINGS

I	100 mA
V	100 V
P_{DISS}	250 mW @ T_A = 25 ^{O}C
T_J	-65 ^{O}C to +175 ^{O}C
T_{STG}	-65 ^{O}C to +175 ^{O}C
θ_{JC}	30 ^{O}C/W

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I_R = 10 µA	100			**V**
C_J	V_R = 50 V f = 1.0 MHz V_R = 40 V			0.15	**pF**
C_P	f = 1.0 MHz		0.10		**pF**
L_S			1.0		**nH**
R_S	I_F = 10 mA f = 500 MHz			1.5	**Ohms**
T_L	I_F = 10 mA I_R = 6.0 mA		100		**nS**
T_{rr}	I_F = 20 mA I_R = 100 mA @ 90%		20		**nS**
I-REGION			12		**µM**